

AMENDMENTS TO THE CLAIMS

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2 The listing of claims will replace all prior versions, and listings, of claims  
3 in the application:  
4

5 Listing of Claims:  
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7 Claims 1-6. (cancelled)  
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9 7. (original): A method of making a semiconductor device comprising:  
10 depositing a layer of oxide proximate a first surface of a semiconductor  
11 substrate;

12 forming a gate oxide layer on the first surface, adjacent to the deposited  
13 oxide layer;

14 forming a pair of active areas in the first surface, adjacent the deposited  
15 oxide layer and gate oxide layer;

16 forming a gate electrode by depositing a conductive layer over the gate  
17 oxide layer;

18 depositing a dielectric layer over the gate electrode, active areas, and  
19 deposited oxide layer; and

20 forming electrical contacts to the pair of active areas and the gate electrode.  
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22 8. (original): The method of Claim 7, further comprising thermally growing a  
23 thermal oxide layer before depositing the layer of oxide on the first surface of the  
24 semiconductor substrate.  
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1 9. (original): The method of Claim 7, wherein the semiconductor substrate is  
2 P type silicon.

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4 10. (original): The method of Claim 7, wherein the active areas are formed by  
5 impurity implant and diffusion.

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7 11. (original): The method of Claim 7, wherein the active areas are n doped  
8 regions.

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10 12. (original): The method of Claim 7, wherein the conductive layer over the  
11 gate oxide layer is polysilicon.

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13 13. (original): The method of Claim 7, wherein the dielectric layer is silicon  
14 dioxide.

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16 Claims 14-18 (cancelled)

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18 19. (currently amended): A method comprising of manufacturing a fluid  
19 ejection device, the method comprising by:

20 depositing a current prevention layer proximate a first surface of a  
21 semiconductor substrate; and

22 forming first and second field effect transistors (FETs), wherein each said  
23 FET includes a gate electrode with associated active areas formed in the first  
24 surface of the semiconductor substrate having the deposited current prevention  
25 layer, wherein the current prevention layer includes a region that minimizes

1 current flow between the active areas of the first FET with respect to the active  
2 areas of the second FET; and  
3 forming a firing chamber above the current prevention layer.

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5 20. (original): The method of Claim 19, wherein the current prevention layer is  
6 a dielectric.

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8 21. (original): The method of Claim 19, wherein the current prevention layer is  
9 an oxide.

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11 22. (currently amended): A method comprising:  
12 depositing a layer of oxide proximate a first surface of a semiconductor  
13 substrate;  
14 exposing a portion of the first surface of the semiconductor substrate; and  
15 forming a field effect transistor (FET) on the exposed portion of the first  
16 surface of the substrate having the deposited oxide layer, wherein the FET  
17 includes a gate electrode with associated active areas formed after the exposing in  
18 the first surface of the semiconductor substrate.

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20 23. (previously presented): A product formed by the method of Claim 22.

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22 24. (previously presented): A method of making a semiconductor device  
23 comprising:  
24 depositing a layer of oxide proximate a first surface of a semiconductor  
25 substrate;

1 exposing a portion of the first surface of the semiconductor substrate;  
2 forming a gate oxide layer on the exposed portion of the first surface,  
3 adjacent to the deposited oxide layer;  
4 forming a pair of active areas in the exposed portion of the first surface,  
5 adjacent the deposited oxide layer and gate oxide layer;  
6 forming a gate electrode by depositing a conductive layer over the gate  
7 oxide layer;  
8 depositing a dielectric layer over the gate electrode, active areas, and  
9 deposited oxide layer; and  
10 forming electrical contacts to the pair of active areas and the gate electrode.

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12 25. (previously presented): The method of Claim 24, further comprising  
13 thermally growing a thermal oxide layer before depositing the layer of oxide on  
14 the first surface of the semiconductor substrate.

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16 26. (previously presented): The method of Claim 24, wherein the  
17 semiconductor substrate is P type silicon.

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19 27. (previously presented): The method of Claim 24, wherein the active areas  
20 are formed by impurity implant and diffusion.

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22 28. (previously presented): The method of Claim 24, wherein the active areas  
23 are n doped regions.

1 29. (previously presented): The method of Claim 24, wherein the conductive  
2 layer over the gate oxide layer is polysilicon.

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4 30. (previously presented): The method of Claim 24, wherein the dielectric  
5 layer is silicon dioxide.

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7 31. (previously presented): A semiconductor device produced by the method of  
8 claim 24.

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10 32. (previously presented): A semiconductor device produced by the method  
11 of claim 7.

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13 33. (previously presented): A fluid ejection device produced by the method of  
14 claim 19.

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